

P-Channel Enhancement Mode Field Effect Transistor

FEATURES

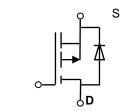
- Super high dense cell design for low RDS(ON)
- Rugged and reliable
- Simple drive requirement
- SOT-23 package

PRODUCT SUMMARY								
V _{DSS}	ΙD	$RDS(ON)$ (m Ω) Typ						
-28V -	5.6A	45@ VGS=-10V						
		55 @ VGS=-4.5V						



NOTE: The MT6401 is available in a lead-free package





ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter Sym	bol	Limit	Unit		
Drain-Source Voltage	Vds	-28	V		
Gate-Source Voltage	Vgs	±20	V		
Drain Current-Continuous ^a @Tj=125°C	Id	ID -5.6			
- Pulse $d^{\it b}$	Ідм	-25	A		
Drain-source Diode Forward Current ^a	Is	-1.5	A		
Maximum Power Dissipation ^a	PD	W			
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 to 150	°C		

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to Ambient ^a Rth	JA	90	°C/W
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ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise noted)

Parameter Sym	bol	Condition	Min	Тур	Max	Unit			
OFF CHARACTERISTICS									
Drain-Source Breakdown Voltage	BVDSS	V _{GS} =0V,I _D =-250μA		-28		V			
Zero Gate Voltage Drain Current	IDSS	V _{DS} =-30V,V _{GS} =0V			1	μA			
Gate-Body Leakage	Igss	V _{GS} =±10V,V _{DS} =0V			±100	nA			
ON CHARACTERITICS									
Gate Threshold Voltage	V _G s(th) V	$_{DS}$ = V_{GS} , I_{D} =-250 μA	-1.2		-2.0	V			
Drain-Source On-State Resistance	RDS(ON)	Vgs=-10V,ID=-4.6A		45	50	O			
Drain-source On-state Resistance	KDS(ON)	V _G S=-4.5V,I _D =-3.0A		55	60	mΩ			
Forward Transconductance	gFS	Vgs=-10V,ID=-1.7A		17		S			
DAYNAMIC CHARACTERISTICS									
Input Capacitance	Ciss			1226		pF			
Output Capacitance	Coss	$V_{DS}=-15V,V_{GS}=0V$ f=1.0MHz		187		pF			
Reverse Transfer Capacitance	Crss	1 1.000112		91		pF			
SWITCHING CHARACTERISISTICS	<u>. </u>								
Turn-On Delay Time	td(ON)	V _{DD} =-15V		5.9		ns			
Rise Time	tr	ID=-1.0A,		6.9		ns			
Turn-Off Delay Time	td(off)	V _{GEN} =-10V R _L =150hm		48		ns			
Fall Time	tf	RGEN=60hm		16		ns			
Total Gate Charge	Qg			9.8		nC			
Gate-Source Charge	Qgs	V _{DS} =-15V,I _D =-1.7A V _{GS} =-10V		1.8		nC			
Gate-Drain Charge	Qgd	100 -101		4.5		nC			

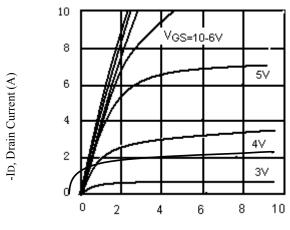


ELECTRICAL CHARACTERICS (TA=25°C unless otherwise noted)

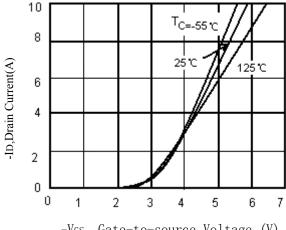
Parameter Sym	bol	Condition	Min	Тур	Max	Unit				
DRAIN-SOURCE DIODE CHARACTERISTICS										
Diode Forward Voltage	Vsd	Vgs=0V,Is=-1.25A		-0.8	-1.2	V				

Notes

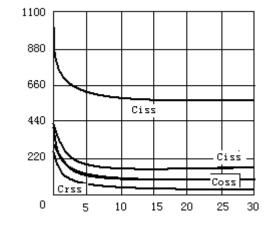
- a. Surface Mounted on FR4 Board, t≦10sec
- b. Pulse Test: Pulse Width ≤ 300Us, Duty Cycle ≤ 2%
- c. Guaranteed by design, not subject to production testing.



- VDS, Drain-to-Source Voltage (V) Figure 1.Output Characteristics



-VGS, Gate-to-source Voltage (V) Figure 2. Transfer Characteristics



- VGS, Drain-to Source Voltage Figure 3. Capacitance

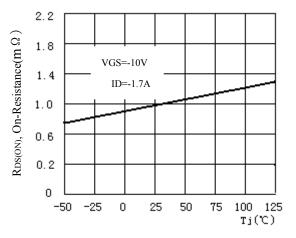
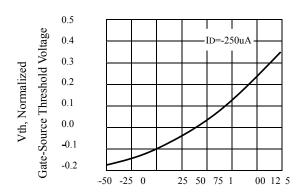
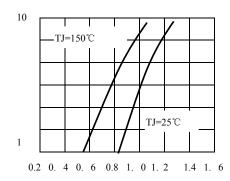


Figure 4. On-Resistance Variation with Temperature

C,Capacitance(pF)

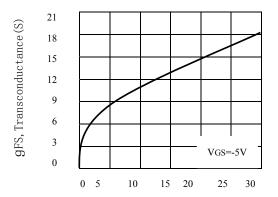


 $Tj.. \ Iunction \ Temperature (^{\mathbb{C}})$ $Figure 5. Gate \ Threshold \ Variation$ $With \ Temperature$



Is-Source Currenti(A)

VSD-Soures-to-Drain Voltage(V)



-IDS, Drain-Source Current (A)
Figure 7. Transconductance Variation

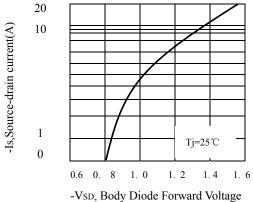


Figure 8. Body Diode Forward Voltage
Variation with Source Current

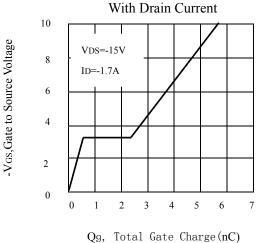
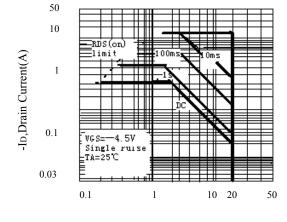
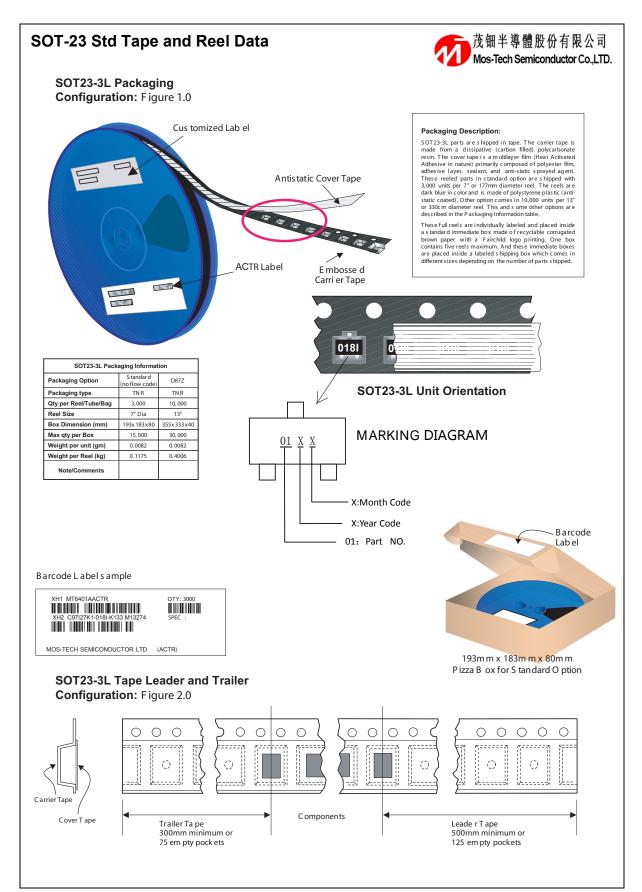


Figure 9. Gate Charge



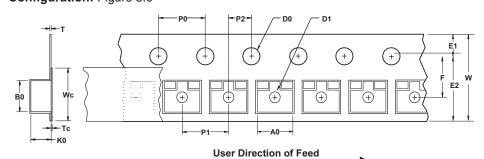
-VDS, Drain-Source Voltage(V)
Figure 10. Maximum Safe Operating Area



SOT-23 Std Tape and Reel Data, continued



SOT23-3L Embossed Carrier Tape Configuration: Figure 3.0



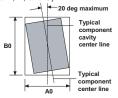
Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).

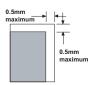


Sketch A (Side or Front Sectional View)

Component Rotation



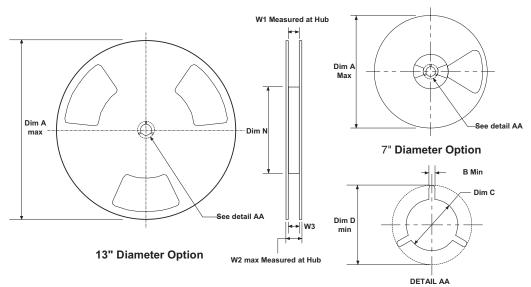
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

SOT23-3L Reel Configuration: Figure 4.0



	Dimensions are in inches and millimeters										
Tape Size	Tape Size Reel Option Dim A Dim B Dim C Dim D Dim N Dim W1 Dim W2 Dim W2 Dim N						Dim W3 (LSL-USL)				
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10. 9		
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10. 9		

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